

NCE N-Channel Enhancement Mode Power MOSFET

Description

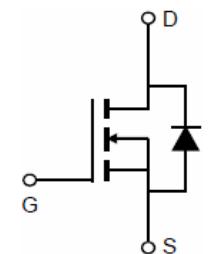
The NCE0103M uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

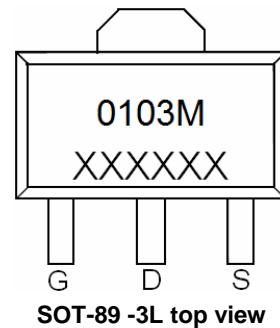
- $V_{DS} = 100V, I_D = 3A$
- $R_{DS(ON)} < 160m\Omega @ V_{GS}=10V$ (Typ:136mΩ)
- $R_{DS(ON)} < 170m\Omega @ V_{GS}=4.5V$ (Typ:140mΩ)
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



SOT-89 -3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
0103M	NCE0103M	SOT-89-3L	Ø180mm	12mm	1000units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	3	A
Drain Current-Pulsed (Note 1)	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83	°C/W
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA

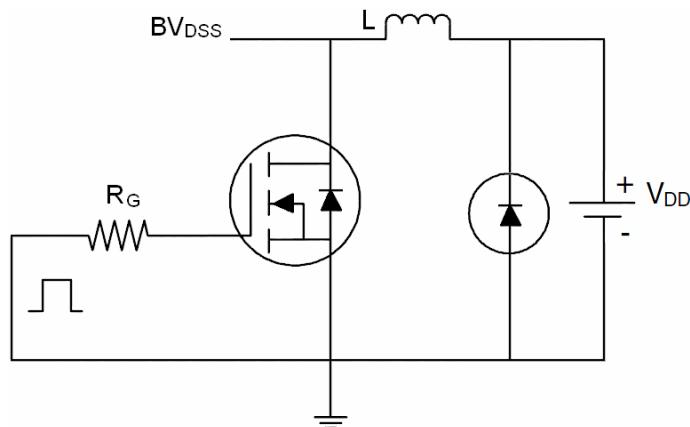
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.8	1.1	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3A$	-	136	160	$m\Omega$
		$V_{GS}=4.5V, I_D=3A$	-	140	170	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=3A$	-	5	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, F=1.0MHz$	-	650	-	PF
Output Capacitance	C_{oss}		-	24	-	PF
Reverse Transfer Capacitance	C_{rss}		-	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, R_L=19\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	6	-	nS
Turn-on Rise Time	t_r		-	4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=3A, V_{GS}=10V$	-	20	-	nC
Gate-Source Charge	Q_{gs}		-	2.1	-	nC
Gate-Drain Charge	Q_{gd}		-	3.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=3A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	3	A

Notes:

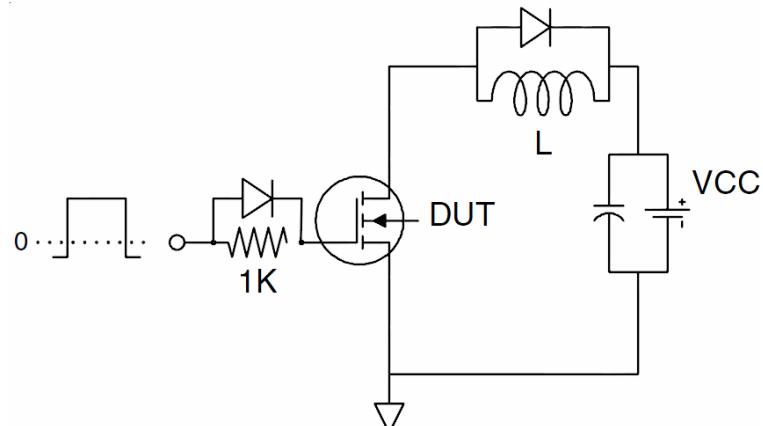
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to productio

Test Circuit

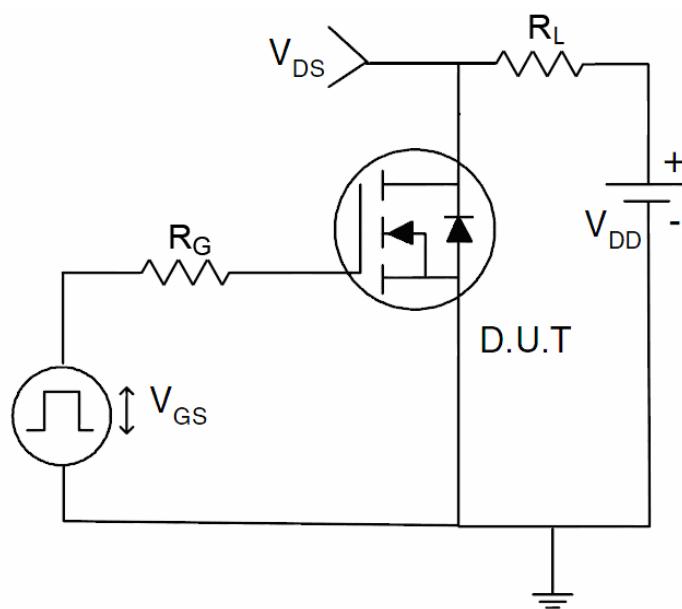
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

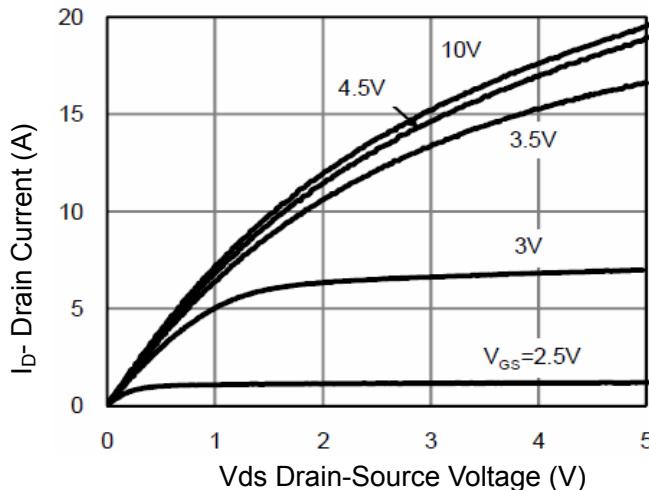


Figure 1 Output Characteristics

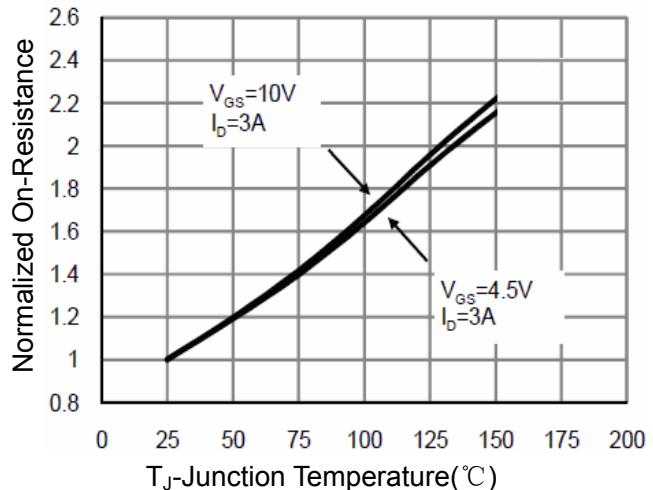


Figure 4 $R_{DS(on)}$ -Junction Temperature

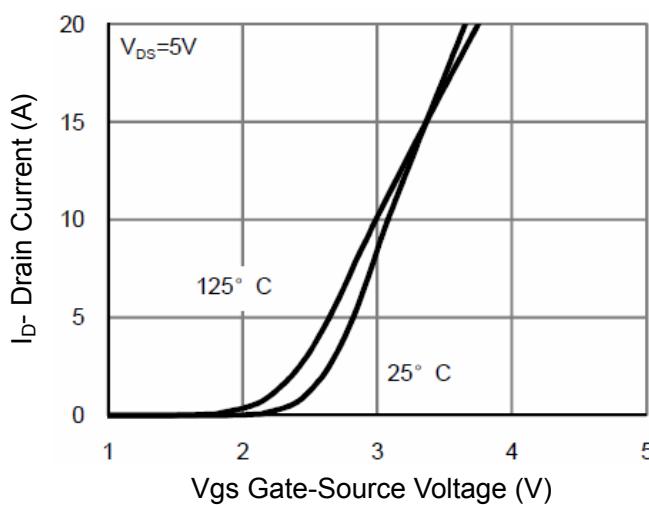


Figure 2 Transfer Characteristics

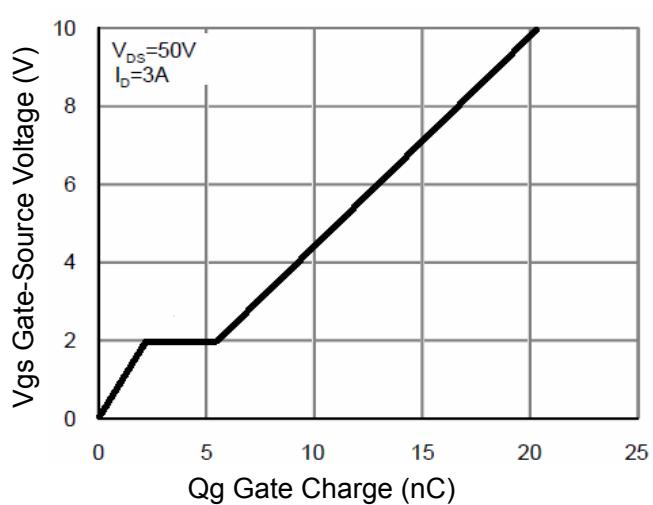


Figure 5 Gate Charge

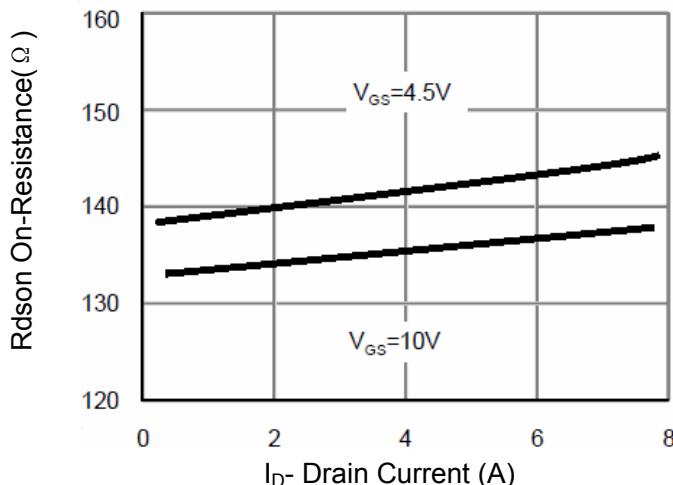


Figure 3 $R_{DS(on)}$ -Drain Current

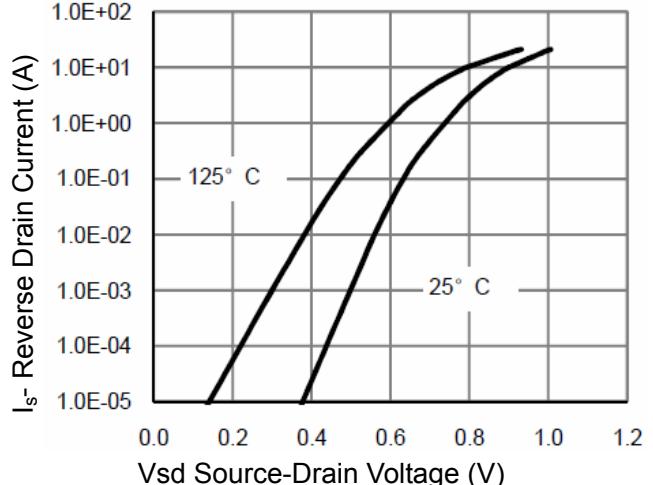
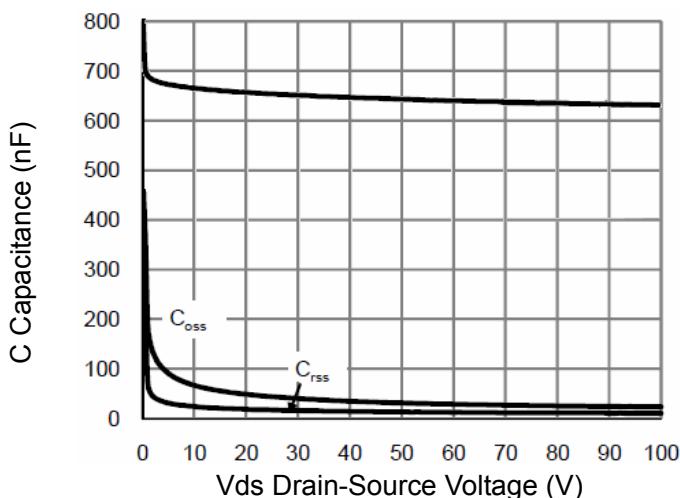
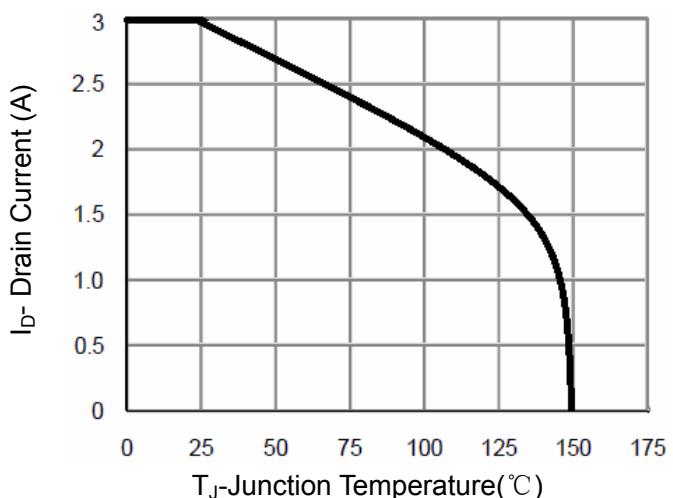
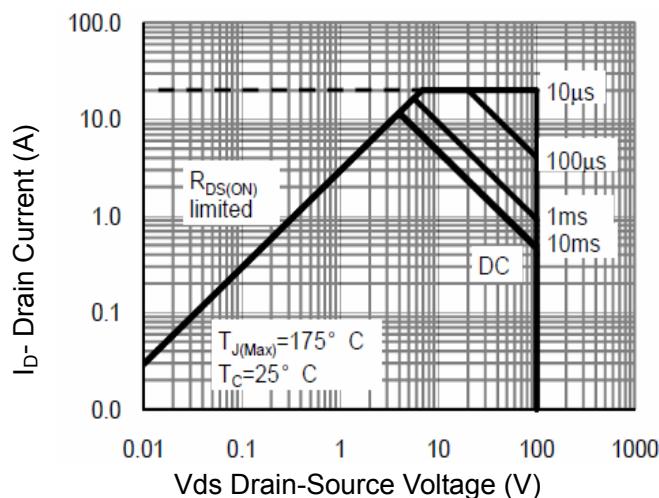
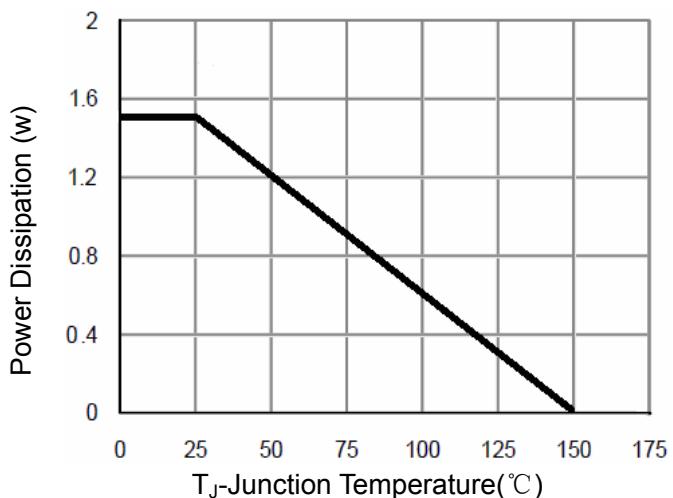
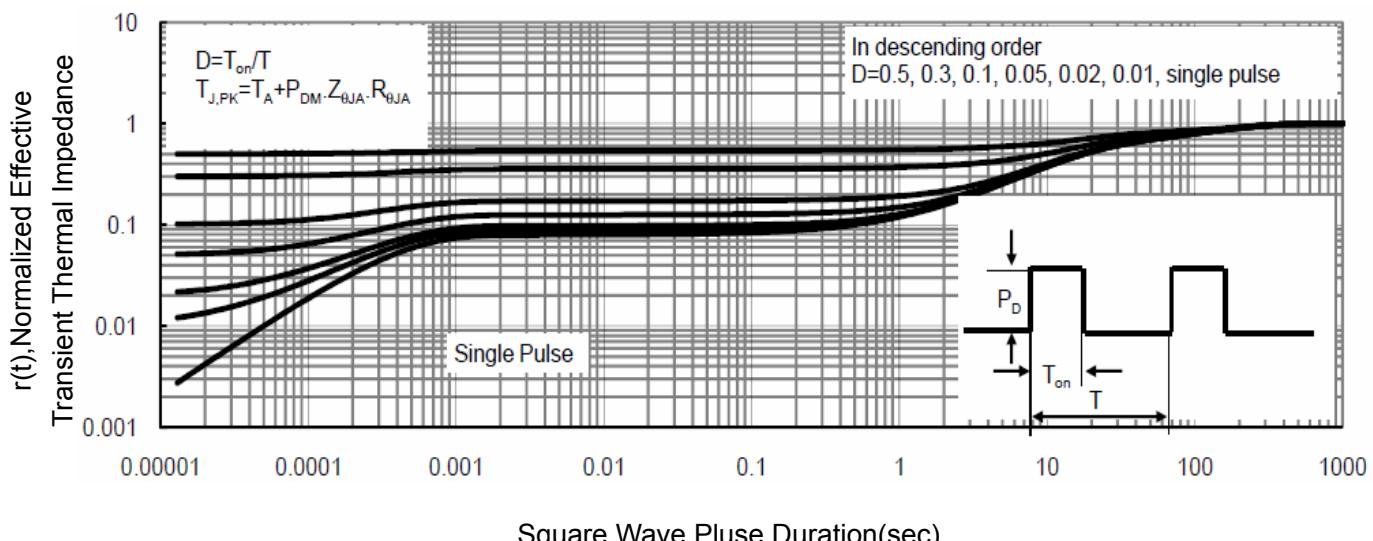
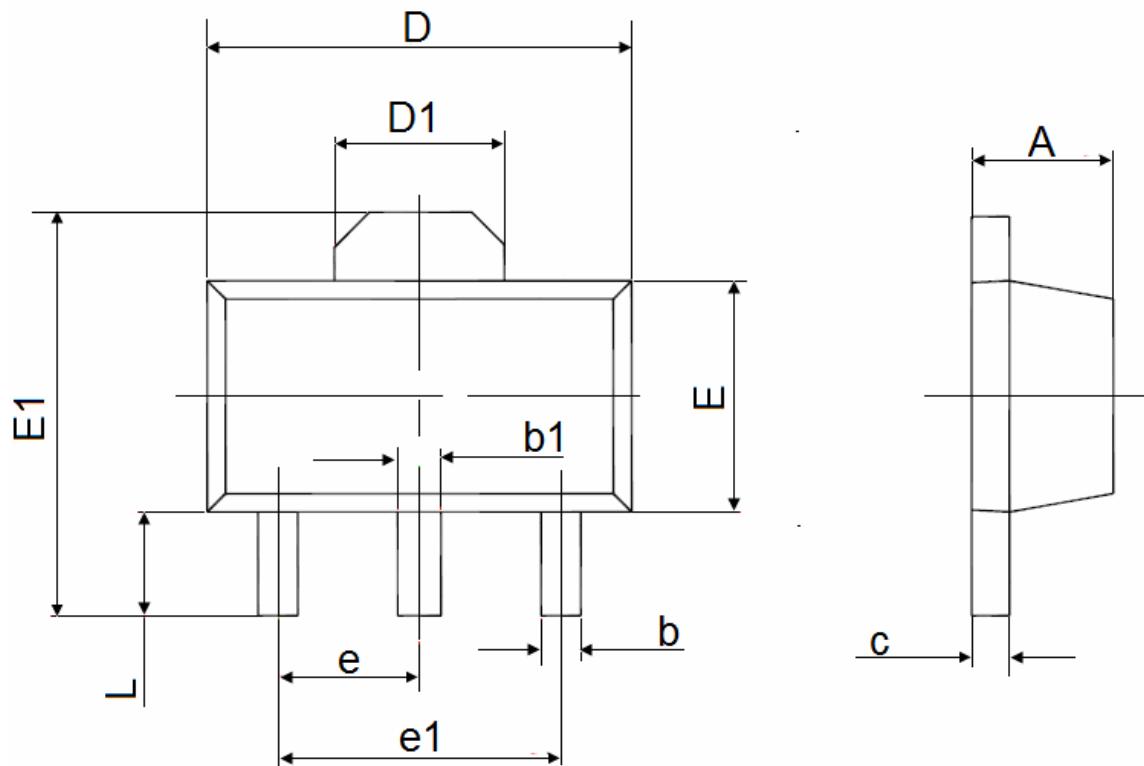


Figure 6 Source-Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 BV_{DSS} vs Junction Temperature

Figure 8 Safe Operation Area

Figure 10 Power De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance

SOT-89-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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